

Towards the Identification of the Dominant Donor in G

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. Materials Research Society Symposia Proceedings, 1995, 395, 351.	0.1	40
2	Electronic Structure of a Nitrogen Vacancy in Cubic Gallium Nitride. Materials Research Society Symposia Proceedings, 1995, 395, 509.	0.1	0
3	Spatially-Resolved Photoluminescence and Raman Study on the GaN/Substrate Interface. Materials Research Society Symposia Proceedings, 1995, 395, 577.	0.1	0
4	Light Generating Carrier Recombination and Impurities in Wurtzite GaN/Al ₂ O ₃ Grown by MOCVD. Materials Research Society Symposia Proceedings, 1995, 395, 633.	0.1	34
5	Growth and Properties of Bulk Single Crystals of GaN. Materials Research Society Symposia Proceedings, 1995, 395, 15.	0.1	6
6	Low-Temperature OMCVD of InN Thin Films from the Novel Air-Stable Single-Molecule Precursor Azido{bis[(3-dimethylamino)propyl]}indium, (N ₃)In[(CH ₂) ₃ NMe ₂] ₂ . Chemistry of Materials, 1996, 8, 1356-1359.	6.7	36
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